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(54) Title: A METHOD FOR TREATING A DEPOSITED FILM FOR RESISTIVITY REDUCTION

(57) Abstract

A method for reducing the resistivity of a copper layer on a wafer. A moisture containing seed layer of copper is formed over a layer of material on a wafer. The copper seed layer is treated by either heat or ions from a plasma to anneal out moisture thereby reducing its resistivity and improving its adhesion to the underlying layer. A moisture free copper layer is then deposited on top of the "clean" or treated copper seed layer.

